

September 22-27, 2019, Germany Seehotel Zeuthen



18th Conference Gettering and Defect Engineering in Semiconductor Technology



Scope

The GADEST conference series provides a forum for interaction between scientists and engineers engaged in the field of semiconductor defect physics, materials science and device technology. The conference is focused on fundamental aspects as well as technological problems associated with defects in electronic materials and devices ranging from microelectronics to photovoltaics.

Topics

Optimization of Si as host material for improved electronic and photovoltaic device function

- crystal growth
- defect and impurity engineering
- stress engineering
- source-drain and channel engineering
- optimization of doping profiles
- interface and gate engineering

Design of heterosystems including material components other than Si as host material for improved and new device functionalities

- high frequency Si/Ge-electronics on Si, high mobility channel materials

- heterogeneously integrated (III - V / Si) photonics
- heavily doped carbon nanotubes as contacts.

Basic research on device physics, point defects, getter effects, and extended defects.

- results obtained by spectroscopic methods
- advanced measurement and detection methods
- ab initio calculations and predictive modeling

Of course, the topics mentioned are not exhaustive. Any contribution fitting into the focus of the conference is welcome.

Conference Chair
Dr. Gudrun Kissinger

Co-chairs
Dr. Dawid Kot, Dr. Marvin Zöllner
and Prof. Hans Richter

Local Chair
Beate Kuck

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